

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (Original): A laminated piezoelectric device obtained by alternately laminating piezoelectric layers containing Pb and conducting layers containing palladium as a conducting component, wherein

the piezoelectric layer formed between the two conducting layers has layer regions where Pb and Pd are mixed together in interfacial portions thereof relative to said conducting layers, said layer regions having a thickness of not larger than 3% of the thickness of said piezoelectric layer.

2. (Original): A laminated piezoelectric device according to claim 1, wherein said layer regions have a thickness of 1 to 3% of the thickness of said piezoelectric layer.

3. (Original): A laminated piezoelectric device according to claim 1, wherein said piezoelectric layer has a thickness of not smaller than 50  $\mu\text{m}$ .

4. (Original): A laminated piezoelectric device according to claim 1, wherein said piezoelectric layer is formed by a piezoelectric ceramic which has, as a crystal phase, a perovskite composite oxide of an  $\text{ABO}_3$  composition containing Pb in the A-site and Zr and Ti in the B-site, the element ratio (A/B) of the A-site element and the B-site element in said piezoelectric layer being smaller than 1.

5. (Original): A laminated piezoelectric device according to claim 1, wherein said conducting layer has a thickness of not smaller than 1  $\mu\text{m}$ .

6. (Original): A laminated piezoelectric device according to claim 1, wherein said conducting layer contains, as conducting components, an element of the Group VIII of periodic table including at least palladium and an element of the Group Ib of periodic table.

7. (Original): A laminated piezoelectric device according to claim 6, wherein when the content of the element of the Group VIII is denoted by M1 mass% and the content of the element of the Group Tb is denoted by M2 mass%, said conducting layer satisfies the following conditions:

$$0.001 \leq M1 \leq 15,$$

$$85 \leq M2 \leq 99.999,$$

$$M1 + M2 = 100 \text{ mass } \%$$

8. (Original): A laminated piezoelectric device according to claim 6, wherein said conducting layer contains at least one kind of element selected from the group consisting of Ni, Pt, Rh, Ir, Ru and Os as well as palladium as the elements of the Group VIII of periodic table, and at least one kind of Cu, Ag or Au as an element of the Group Ib of periodic table.

9. (Original): A laminated piezoelectric device according to claim 1, wherein said piezoelectric layer contains fine voids distributed in an amount of not larger than 15% per the volume of the piezoelectric layer.

10. (Original): A laminated piezoelectric device according to claim 9, wherein said voids are distributed in a flat shape with the direction of thickness of the piezoelectric layer as a short axis and the direction of surface of the piezoelectric layer as a long axis.

11. (Original): A laminated piezoelectric device according to claim 10, wherein when the length of the short axis of said void is denoted by  $a$  and the length of the long axis thereof by  $b$ , there hold  $b/a \leq 4$  and  $b \leq 3 \mu\text{m}$ .

12-14. (Canceled).

15. (Original): An injection apparatus comprising a container having an injection hole, a laminated piezoelectric device of claim 1 contained in said container, and a valve for injecting a liquid through said injection hole being driven by said laminated piezoelectric device.

16. (Previously presented): A laminated piezoelectric device according to claim 1, wherein said piezoelectric device is formed by a piezoelectric layers having, as a crystal phase, a perovskite composition oxide of an  $\text{ABO}_3$  composition containing Pb in the A-site and Zr and Ti in the B-site, the average valency of the element species constituting the B-site being larger than 4.

17. (Previously presented): A laminated piezoelectric device according to claim 16, wherein said average valency of the element species constituting the B-site is in the range of 4.002 to 4.009.

18. (Previously presented): A laminated piezoelectric device according to claim 1, wherein said conducting layers contain an inorganic derivative component.

19. (Previously presented): A laminated piezoelectric device according to claim 18, wherein said inorganic derivative component is a perovskite composite oxide.

20. (Previously presented): A laminated piezoelectric device according to claim 18, wherein said inorganic derivative component is contained in an amount of

not larger than 5 mass% per the total amount of the conducting components constituting the conducting layers

21. (Previously presented): A laminated piezoelectric device according to claim 18, wherein the grain size of the inorganic derivative component is smaller than the average grain size of the piezoelectric ceramic forming the piezoelectric layer.

22. (Previously presented): A laminated piezoelectric device according to claim 11, wherein the length (a) of the short axis of said void is in the range of  $a \leq 0.5t_0$  ( $t_0$ : the thickness of the piezoelectric layer).

23-24. (Canceled).